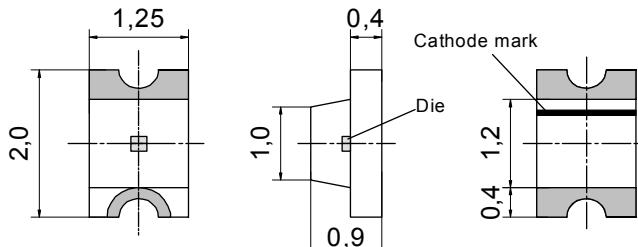


Radiation	Type	Technology	Case
Infrared	SMD	AlGaAs/AlGaAs	SMD 0805

 <p>All dimensions in mm Tolerances: <math>\pm 0,1\text{mm}</math></p>	<b>Description</b> High-power, high speed LED in standard SMD package, compact design allows for easy circuit board mounting or assembling of arrays
	<b>Applications</b> Optical communications, remote control and light barriers, measurement applications and security systems, automation

### Absolute Maximum Ratings

at  $T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
DC forward current		$I_F$	50	mA
Peak forward current	$t_p \leq 10 \mu\text{s}, t_p/T \leq 0.1$	$I_{FM}$	100	mA
Power dissipation		P	100	mW
Operating temperature range		$T_{\text{amb}}$	-40 to +85	°C
Storage temperature range		$T_{\text{stg}}$	-55 to +100	°C

### Electrical and Optical Characteristics

at  $T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1,6	1,9	V
Reverse voltage	$I_F = 100 \mu\text{A}$	$V_R$	5			V
Radiant power	$I_F = 100 \text{ mA}$	$\Phi_e$	4.6	6.0		mW
Radiant intensity	$I_F = 100 \text{ mA}$	$I_e$	1.25	1.6		mW/sr
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$	860	875	890	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		30		nm
Viewing angle	$I_F = 100 \text{ mA}$	$\varphi$		120		deg.
Switching time	$I_F = 100 \text{ mA}$	$t_r, t_f$		20		ns

Note: All measurements carried out with EPIGAP equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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